The GreenMOS® high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.
The GreenMOS® Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

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Absolute Maximum Ratings at T_j=25 unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	800	V
Gate-source voltage	V_{GS}	±30	V
Continuous drain current[1], T_C=25 °C	I_D	5	A
Continuous drain current[1], T_C=100 °C		3.2	
Pulsed drain current[2], T_C=25 °C	$I_{D,\ pulse}$	15	A
Continuous diode forward current[1], T_C=25 °C	I_S	5	A
Diode pulsed current[2], T_C=25 °C	$I_{S,\ pulse}$	15	

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		647.4		pF	V_{GS}=0 V, V_{DS}=50 V, 00 kHz
Output capacitance	C_{oss}		36.1		pF	
Reverse transfer capacitance	C_{rss}		1.5		pF	
Turn-on delay time	$t_{d(on)}$		31.3		ns	V_{GS}=10 V, V_{DS}=400 V, R_G I_D=4 A
Rise time	t_r		16.4		ns	
Turn-off delay time	$t_{d(off)}$		54.6		ns	
Fall time	t_f		7.0		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		11.7		nC	V_{GS}=10 V, V_{DS}=400 V, I_D=4 A
Gate-source charge	Q_{gs}		2.8		nC	
Gate-drain charge	Q_{gd}		4.4		nC	
Gate plateau voltage	$V_{plateau}$		5.8		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	I_S=5 A, V_{GS}=0 V
Reverse recovery time	t_{rr}		216.5		ns	V_R=400 V, I_S=4 A,
Reverse recovery charge	Q_{rr}		1.9		C	
Peak reverse recovery current	I_{rrm}		17.0		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) The value of R is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.
5) V_{DD}=100 V, V_{GS}=10 V, L=60 mH, starting T_j=25 °C.

Electrical Characteristics Diagrams

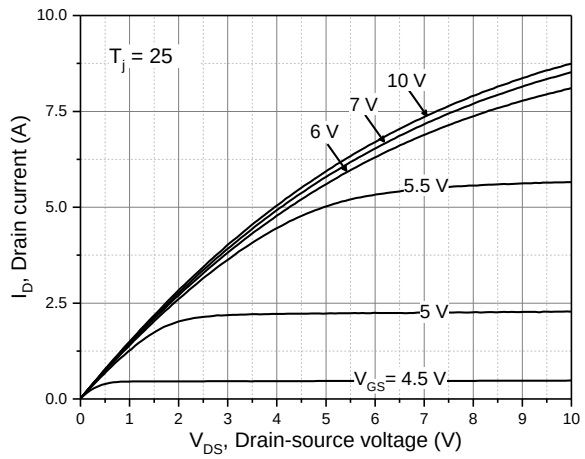

Figure 1. Typ. output characteristics

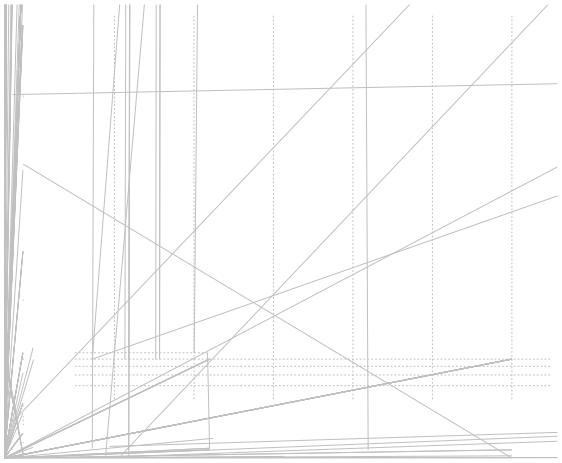

Figure 2. Typ. transfer characteristics

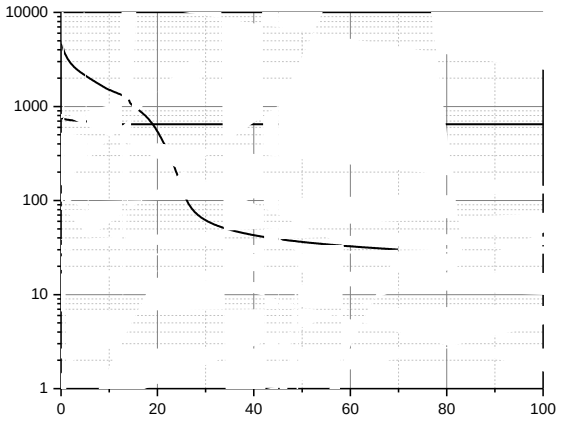

Figure 3. Typ. capacitances

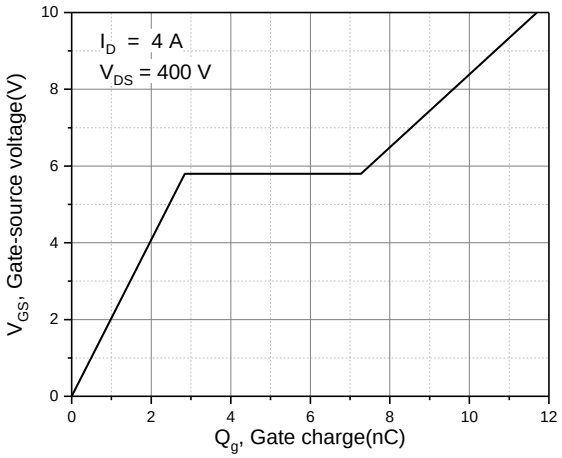

Figure 4. Typ. gate charge

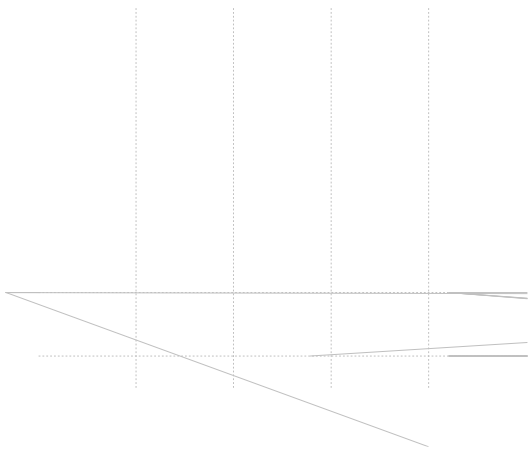

Figure 5. Drain-source breakdown voltage

Figure 6. Drain-source on-state resistance

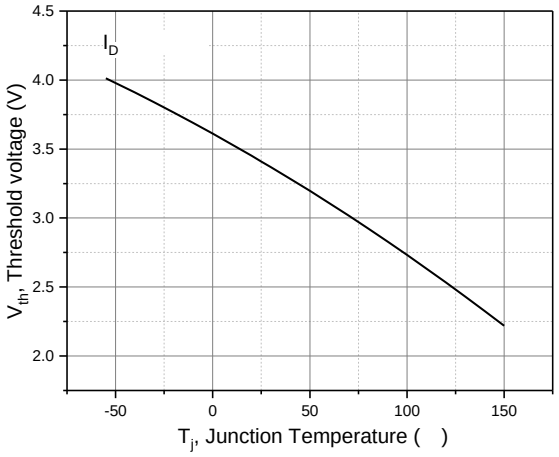

Figure 7. Threshold voltage

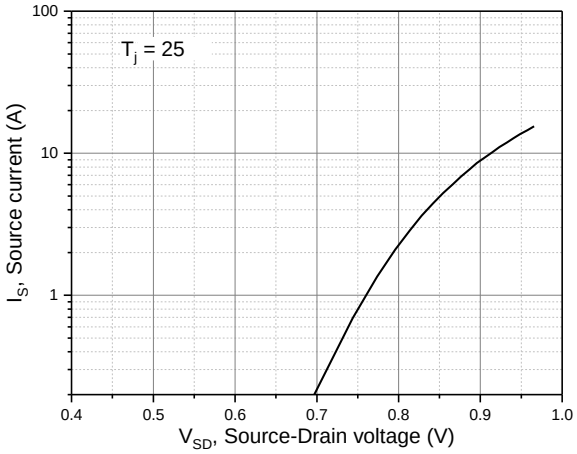

Figure 8. Forward characteristic of body diode

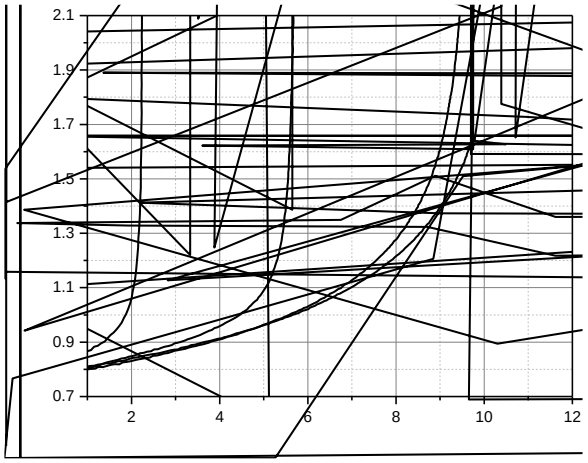

Figure 9. Drain-source on-state resistance

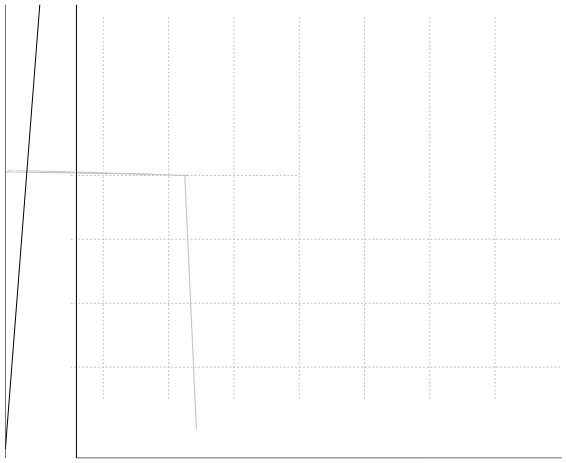

Figure 10. Drain current

Figure 11. Safe operation area T_C=25 °C

Test circuits and waveforms

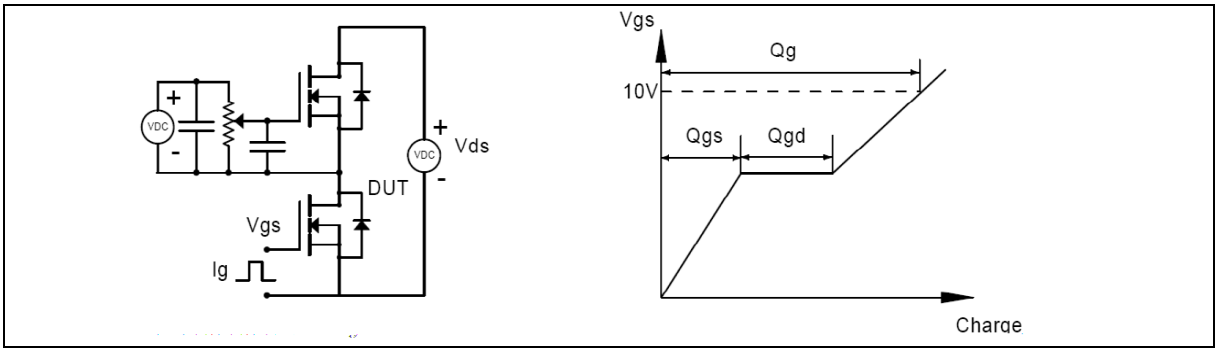

Figure 1. Gate charge test circuit & waveform

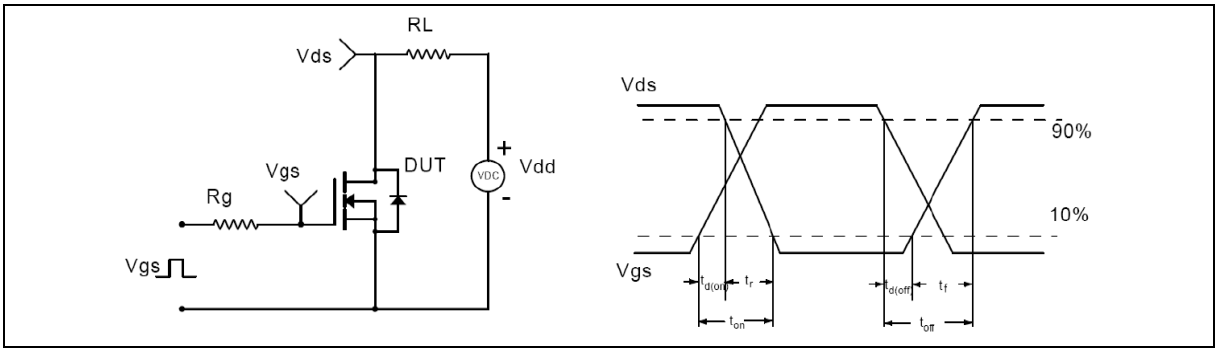

Figure 2. Switching time test circuit & waveforms

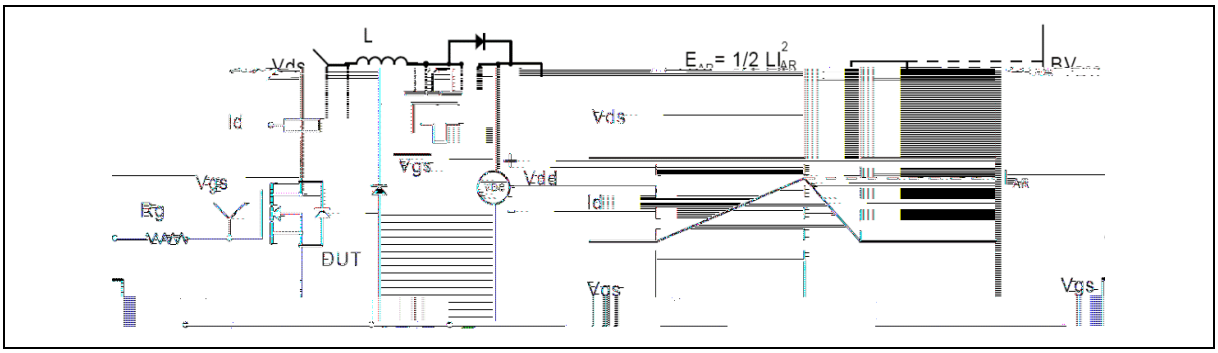

Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

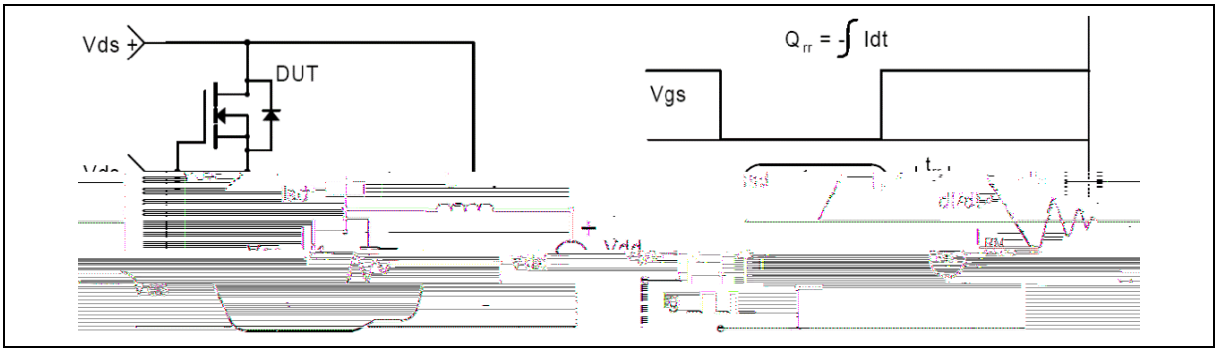

Figure 4. Diode reverse recovery test circuit & waveforms

Package Information

Symbol	mm		
	Min	Nom	Max
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63		

Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO252-C	2500	2	5000	5	25000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG80R900DF	TO252	yes	yes	yes